

isc Silicon NPN Power Transistor

DESCRIPTION

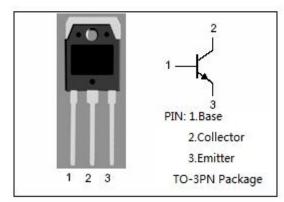
- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 85V(Min)
- · Good Linearity of hFE
- · High Current Capability
- · Wide Area of Safe Operation
- · Complement to Type 2SB775
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

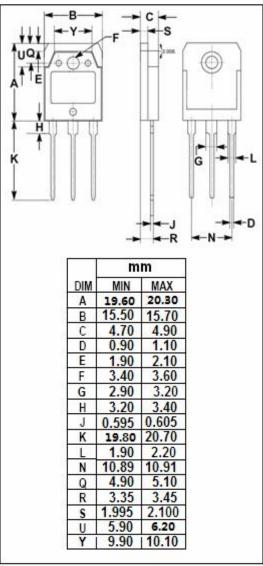
APPLICATIONS

• Designed for 35W audio frequency output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	85	V
V _{EBO}	Emitter-Base Voltage	V	
Ic	Collector Current-Continuous	Α	
I _{CP}	Collector Current-Pulse	10	А
Pc	Collector Power Dissipation @ T _C =25℃ 60		W
TJ	Junction Temperature	150	$^{\circ}$ C
T _{stg}	Storage Temperature Range -40~150		$^{\circ}$ C







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2SD895

ELECTRICAL CHARACTERISTICS

 T_{C} =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA ; R _{BE} =∞	85			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	100			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.4A			2.0	V
V _{BE(on)}	Base -Emitter On Voltage	I _C = 1A; V _{CE} = 5V			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			100	μА
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			100	μ А
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	60		200	
h _{FE-2}	DC Current Gain	I _C = 3A; V _{CE} = 5V	20			
Сов	Output Capacitance	V _{CB} = 10V; f _{test} = 1.0MHz		160		pF
f⊤	Current-Gain—Bandwidth Product	Ic= 1A; V _{CE} = 5V		15		MHz
Switching times						
ton	Turn-on Time			0.20		μS
tstg	Storage Time	I_{C} = 1A ,R _L = 20 Ω , I_{B1} = I_{B2} = 0.1A,V _{CC} = 20V		3.88		μS
t _f	Fall Time			0.82		μS

♦ h_{FE-1} Classifications

D	E
60-120	100-200

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